

# ZXTP25012EZ

## 20V PNP high gain transistor in SOT89

### Summary

$BV_{CEO} > -12V$

$h_{FE} > 500$

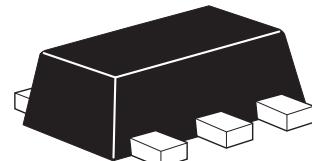
$I_C(\text{cont}) = 4.5A$

$V_{CE(\text{sat})} < -70mV @ 1A$

$R_{CE(\text{sat})} = 45m\Omega$

$P_D = 2.4W$

Complementary part number ZXTN25012EZ

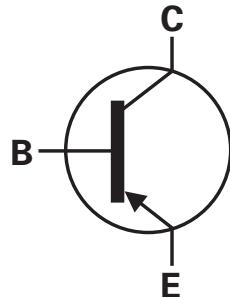


### Description

Packaged in the SOT89 outline this new low saturation 12V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

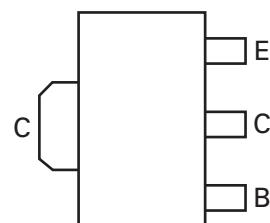
### Features

- 4.5A continuous current
- Up to 10A peak current
- Very low saturation voltages
- High gain



### Applications

- High side switch
- Battery charging
- Regulator circuits
- Buck converters
- MOSFET gate drivers



Pinout - top view

### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25012EZTA	7	12	1000

### Device marking

- 1L4

**Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-Base voltage	$V_{CBO}$	-20	V
Collector-Emitter voltage	$V_{CEO}$	-12	V
Emitter-Base voltage	$V_{EBO}$	-7	V
Continuous Collector current <sup>(c)</sup>	$I_C$	-4.5	A
Base current	$I_B$	-1	A
Peak pulse current	$I_{CM}$	-10	A
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(a)</sup>	$P_D$	1.1	W
Linear derating factor		8.8	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(b)</sup>	$P_D$	1.8	W
Linear derating factor		14.4	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(c)</sup>	$P_D$	2.4	W
Linear derating factor		19.2	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(d)</sup>	$P_D$	4.46	W
Linear derating factor		35.7	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(d)</sup>	$P_D$	19.2	W
Linear derating factor		153	$\text{mW}/^\circ\text{C}$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to 150	$^\circ\text{C}$

**Thermal resistance**

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	117	$^\circ\text{C}/\text{W}$
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	68	$^\circ\text{C}/\text{W}$
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	51	$^\circ\text{C}/\text{W}$
Junction to ambient <sup>(d)</sup>	$R_{\Theta JA}$	28	$^\circ\text{C}/\text{W}$
Junction to case <sup>(e)</sup>	$R_{\Theta JC}$	7.95	$^\circ\text{C}/\text{W}$

**NOTES:**

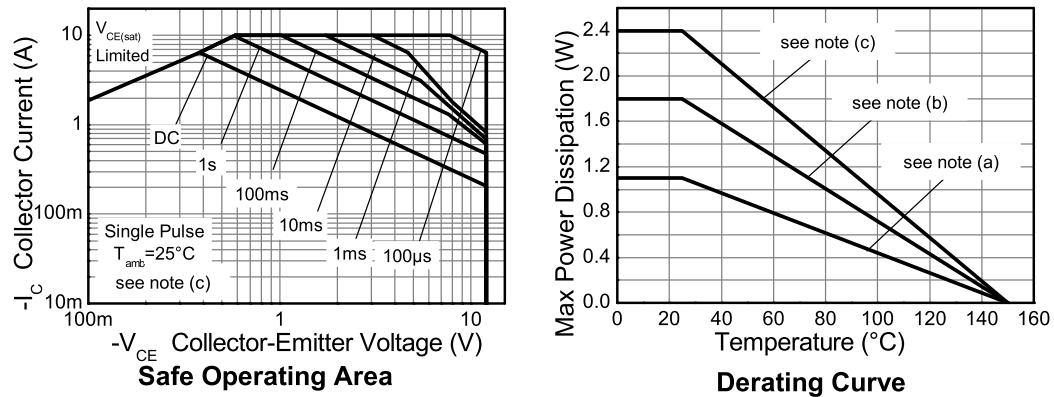
(a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

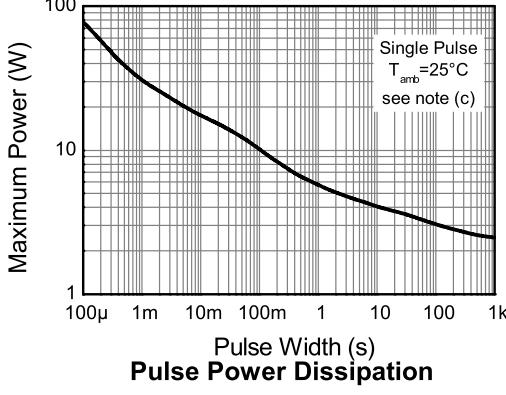
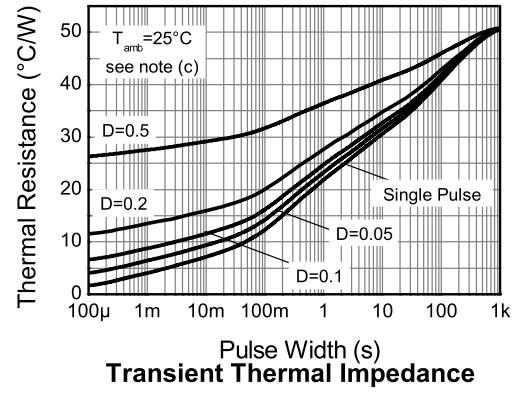
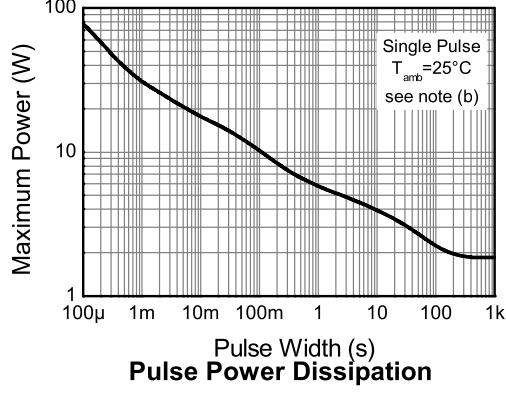
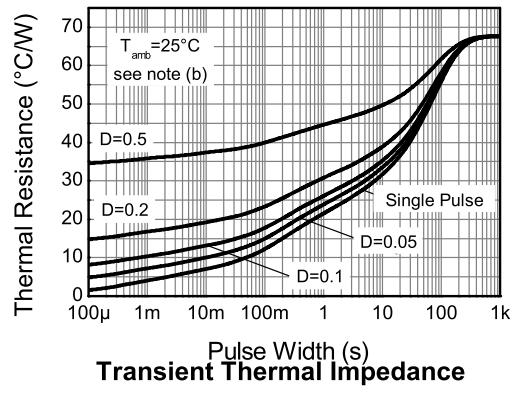
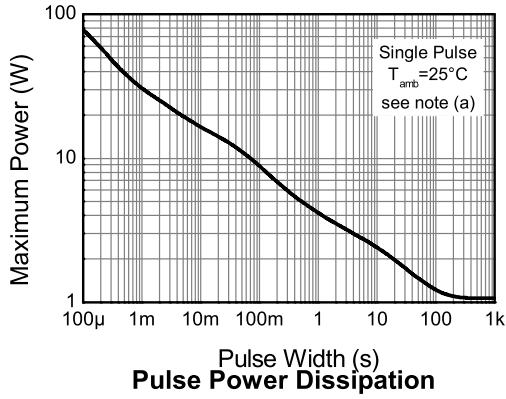
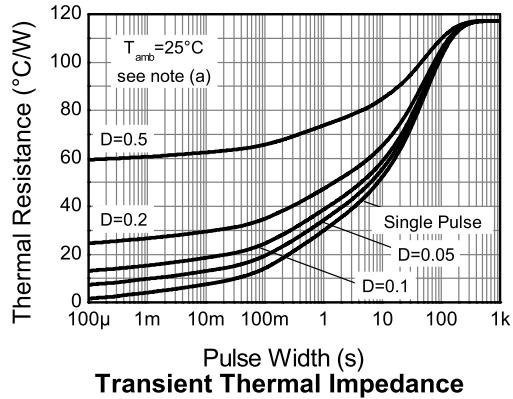
(c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

(d) As (c) above measured at  $t < 5$  seconds.

(e) Junction to case (collector tab). Typical

**Thermal characteristics**

## Thermal characteristics



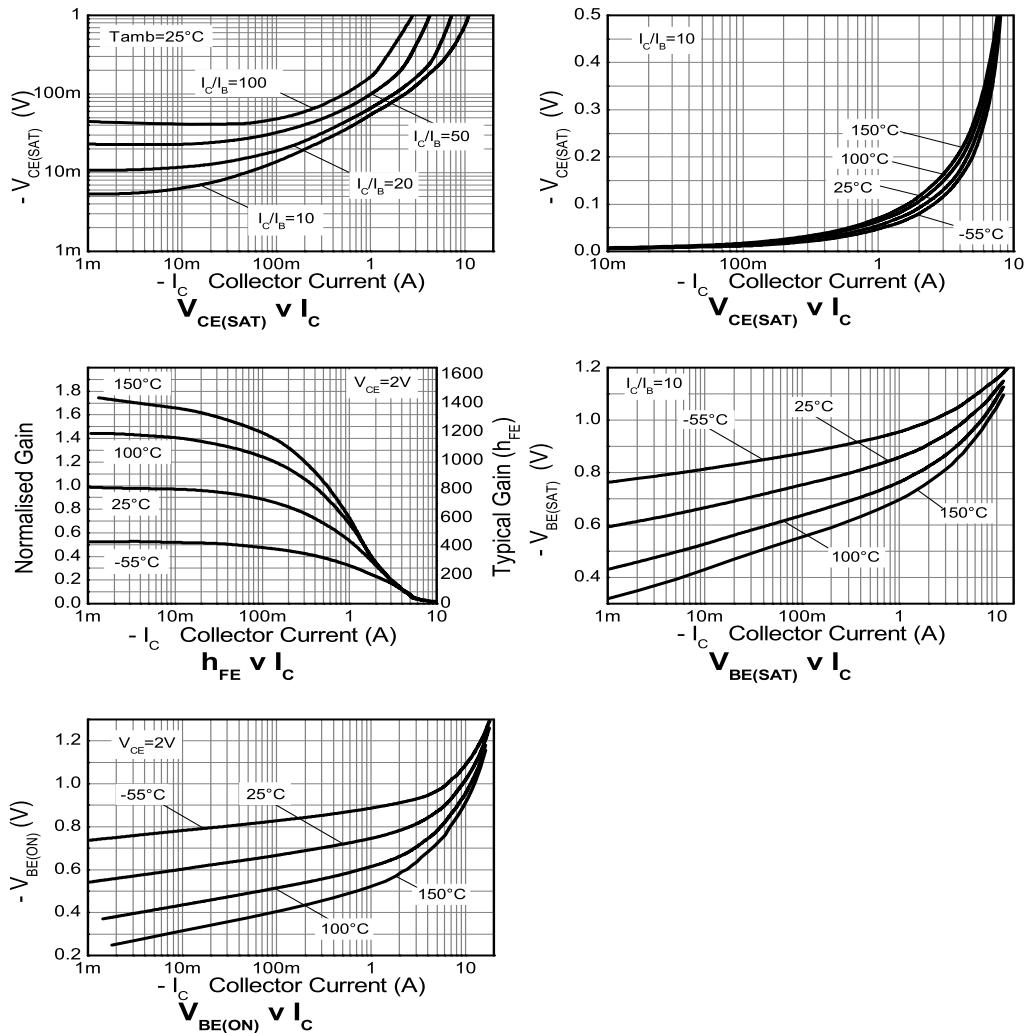
**Electrical characteristics (at  $T_{amb} = 25^\circ C$  unless otherwise stated)**

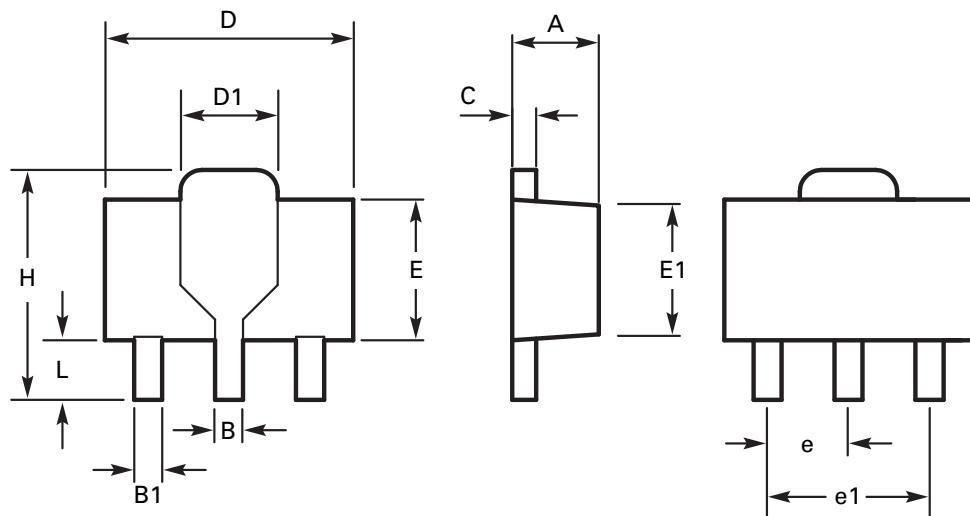
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base breakdown voltage	$BV_{CBO}$	-12	-35		V	$I_C = -100\mu A$
Collector-Emitter breakdown voltage	$BV_{CEO}$	-12	-25		V	$I_C = -10mA$ (*)
Emitter-Base breakdown voltage	$BV_{EBO}$	-7	-8.5		V	$I_E = -100\mu A$
Collector-Base cut-off current	$I_{CBO}$		<-1	-50 -0.5	nA $\mu A$	$V_{CB} = -12V$ $V_{CB} = -12V, T_{amb} = 100^\circ C$
Emitter Base cut-off current	$I_{EBO}$		<-1	-50	nA	$V_{EB} = -5.6V$
Collector-Emitter saturation voltage	$V_{CE(sat)}$		-55 -155 -185 -200	-70 -265 -355 -285	mV mV mV mV	$I_C = -1A, I_B = -100mA$ (*) $I_C = -1A, I_B = -10mA$ (*) $I_C = -2A, I_B = -40mA$ (*) $I_C = -4.5A, I_B = -450mA$ (*)
Base-Emitter saturation voltage	$V_{BE(sat)}$		-990	-1100	mV	$I_C = -4.5A, I_B = -450mA$ (*)
Base-Emitter turn-on voltage	$V_{BE(on)}$		-865	-975	mV	$I_C = -4.5A, V_{CE} = -2V$ (*)
Static forward current transfer ratio	$h_{FE}$	500 300 40	800 450 85 15	1500		$I_C = -10mA, V_{CE} = -2V$ (*) $I_C = -1A, V_{CE} = -2V$ (*) $I_C = -4.5A, V_{CE} = -2V$ (*) $I_C = -10A, V_{CE} = -2V$ (*)
Transition frequency	$f_T$		310		MHz	$I_C = -50mA, V_{CE} = -10V$ $f = 100MHz$
Input capacitance	$C_{ibo}$		127	250	pF	$V_{EB} = -0.5V, f = 1MHz$ (*)
Output capacitance	$C_{obo}$		16.9	30	pF	$V_{CB} = -10V, f = 1MHz$ (*)
Delay time	$t_d$		41		ns	$V_{CC} = -10V, I_C = -1A,$ $I_{B1} = -I_{B2} = -10mA$
Rise time	$t_r$		62		ns	
Storage time	$t_s$		179		ns	
Fall time	$t_f$		65		ns	

**NOTES:**

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

**Typical characteristics**



**Package outline**

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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